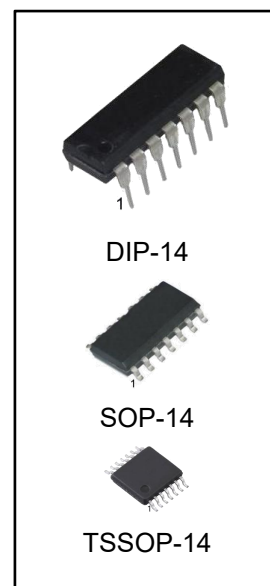


Quad 2-Input NAND Gate with Schmitt-Trigger Inputs

High-Performance Silicon-Gate CMOS

FEATURES

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements as Defined by JEDEC Standard No. 7A
- ESD Performance:
 - HBM > 2000 V;
 - Machine Model > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These are Pb-Free Device



ORDERING INFORMATION

DEVICE	Package Type	MARKING	Packing	Packing Qty
74HC132N	DIP-14	74HC132	TUBE	1000pcs/box
74HC132M/TR	SOP-14	74HC132	REEL	2500pcs/reel
74HC132MT/TR	TSSOP-14	HC132	REEL	2500pcs/reel

GENERAL DESCRIPTION

The 74HC132 is identical in pinout to the LS132. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs. The HC132 can be used to enhance noise immunity or to square up slowly changing waveforms.

PIN CONFIGURATION

DIP-14/SOP-14/TSSOP-14

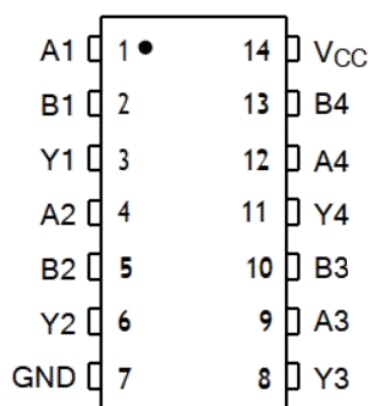
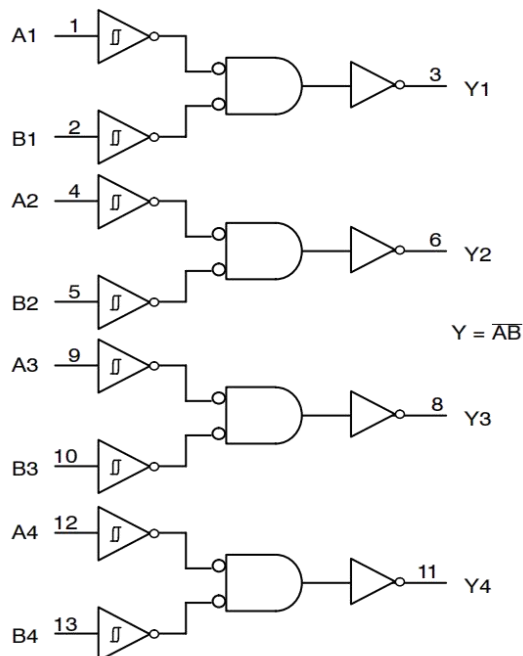


Figure 1. Pin Assignment



PIN 14 = V_{CC};

PIN 7 = GND

Figure 2. Logic Diagram

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	Digital Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage Output in 3-State High or Low State	-0.5 to +7.0 -0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
I _{OUT}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, VCC and GND Pins	±75	mA
I _{GND}	DC Ground Current per Ground Pin	±75	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature Under Bias	+125	°C
θ _{JA}	Thermal Resistance 14-SOP 14-TSSOP	125 170	°C/W
P _D	Power Dissipation in Still Air at 85°C SOP TSSOP	500 450	mW
M _{SL}	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 1) Machine Model (Note 2)	>2000 >200	V
I _{Latchup}	Latchup Performance Above VCC and Below GND at 85°C (Note 3)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22-A114-A.
2. Tested to EIA/JESD22-A115-A.
3. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	–	NoLimit (Note5)	ns

4. When $V_{IN} \sim 0.5 V_{CC}$, $I_{CC} \gg$ quiescent current.

5. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} (V)	Guaranteed Limit		Unit
				-40°C to 25°C	≤85°C	
V _{T+max}	Maximum Positive Going Input Threshold Voltage (Figure 5)	V _{OUT} = 0.1 V I _{OUT} ≤ 20 μA	2.0	1.5	1.5	V
			4.5	3.15	3.15	
			6.0	4.2	4.2	
V _{T+min}	Minimum Positive-Going Input Threshold Voltage (Figure 5)	V _{OUT} = 0.1 V I _{OUT} ≤ 20 μA	2.0	1.0	0.95	V
			4.5	2.3	2.25	
			6.0	3.0	2.95	
V _{T-max}	Maximum Negative-Going Input Threshold Voltage (Figure 5)	V _{OUT} = V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0	0.9	0.95	V
			4.5	2.0	2.05	
			6.0	2.6	2.65	
V _{T-min}	Minimum Negative-Going Input Threshold Voltage (Figure 5)	V _{OUT} = V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0	0.3	0.3	V
			4.5	0.9	0.9	
			6.0	1.2	1.2	
V _{Hmax} (Note 7)	Maximum Hysteresis Voltage (Figure 5)	V _{OUT} = 0.1 V or V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0	1.2	1.2	V
			4.5	2.25	2.25	
			6.0	3.0	3.0	
V _{Hmin} (Note 7)	Minimum Hysteresis Voltage (Figure 5)	V _{OUT} = 0.1 V or V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0	0.2	0.2	V
			4.5	0.4	0.4	
			6.0	0.5	0.5	
V _{OH}	Minimum High-Level Output Voltage	V _{IN} ≤ V _{T-min} or V _{T+max} I _{OUT} ≤ 20 μA	2.0	1.9	1.9	V
			4.5	4.4	4.4	
			6.0	5.9	5.9	
		V _{IN} ≤ -V _{T-min} or V _{T+max} I _{OUT} ≤ 4.0 mA	4.5	3.98	3.84	
			6.0	5.48	5.34	
			6.0	5.48	5.34	

V_{OL}	Maximum Low-Level Output Voltage	$V_{IN} \geq V_T + \max$	2.0	0.1	0.1	V
		$ I_{OUT} \leq 20 \mu A$	4.5	0.1	0.1	
			6.0	0.1	0.1	
		$V_{IN} \geq V_T + \max I_{OUT} \leq 4.0 \text{ mA}$	4.5	0.26	0.33	
		$ I_{OUT} \leq 5.2 \text{ mA}$	6.0	0.26	0.33	
I_{IN}	Maximum Input Leakage Current	$V_{IN} = V_{CC} \text{ or GND}$	6.0	± 0.1	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{IN} = V_{CC} \text{ or GND}$ $I_{OUT} = 0 \mu A$	6.0	2.0	20	μA

6. $V_{Hmin} > (V_{T+min}) - (V_{T-max})$; $V_{Hmax} = (V_{T+max}) + (V_{T-min})$.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

Symbol	Parameter	VCC	Guaranteed Limit		Unit
		(V)	-40°C to 25°C	≤85°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 3 and 4)	2.0	125	155	ns
		4.5	25	31	
		6.0	21	26	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	2.0	75	95	ns
		4.5	15	19	
		6.0	13	16	
C _{in}	Maximum Input Capacitance	—	10	10	pF
C _{PD}	Power Dissipation Capacitance(per Gate)(Note 10)	Typical@25°C,VCC=5.0V			pF
		24			

Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$

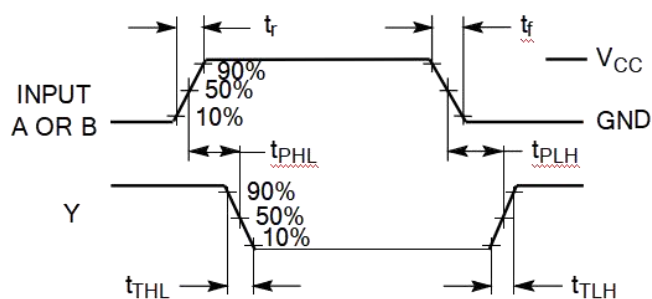
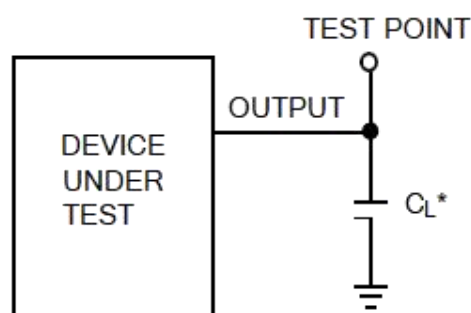
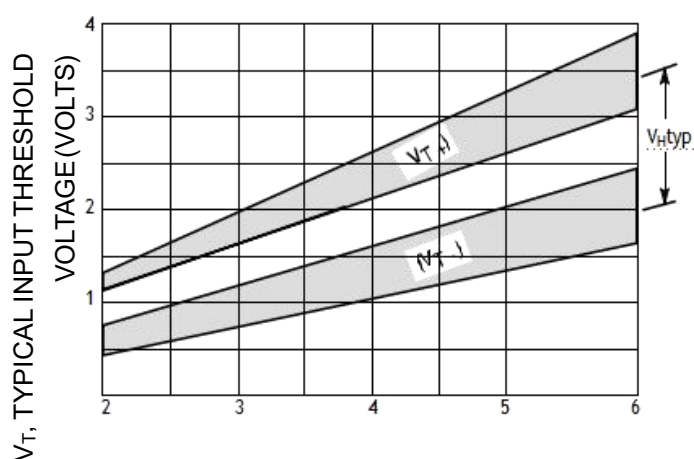


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

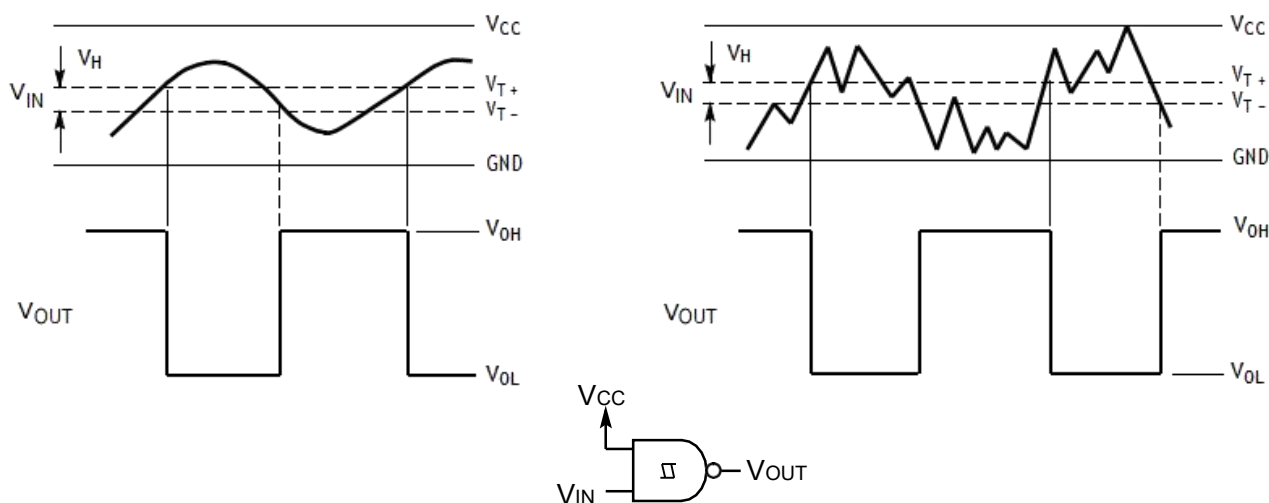
Figure 4. Test Circuit



V_{CC} , POWER SUPPLY VOLTAGE (VOLTS)

$$V_{Htyp} = (V_{T+} - V_{T-})$$

Figure 5. Typical Input Threshold, V_{T+} , V_{T-} Versus Power Supply Voltage



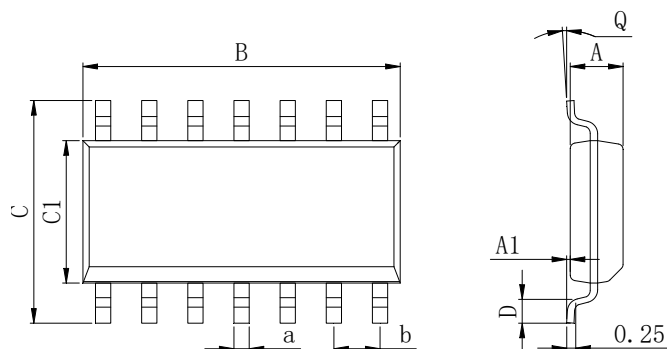
(A) A SCHMITT TRIGGER SQUARES UP INPUTS WITH SLOW RISE AND FALL TIMES

(B) A SCHMITT TRIGGER OFFERS MAXIMUM NOISE IMMUNITY

Figure 6. Typical Schmitt-Trigger Applications

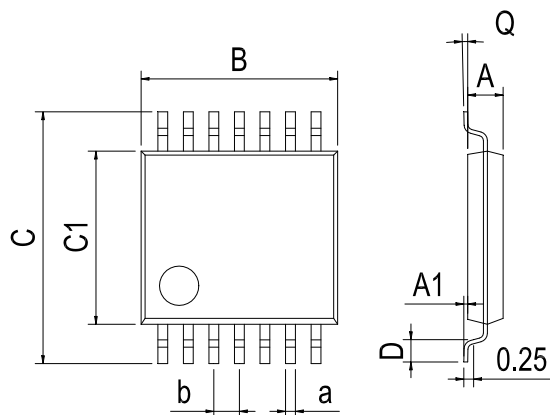
PHYSICAL DIMENSIONS

SOP-14



Dimensions In Millimeters(SOP-14)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	8.75	6.20	4.00	0.80	8°	0.45	

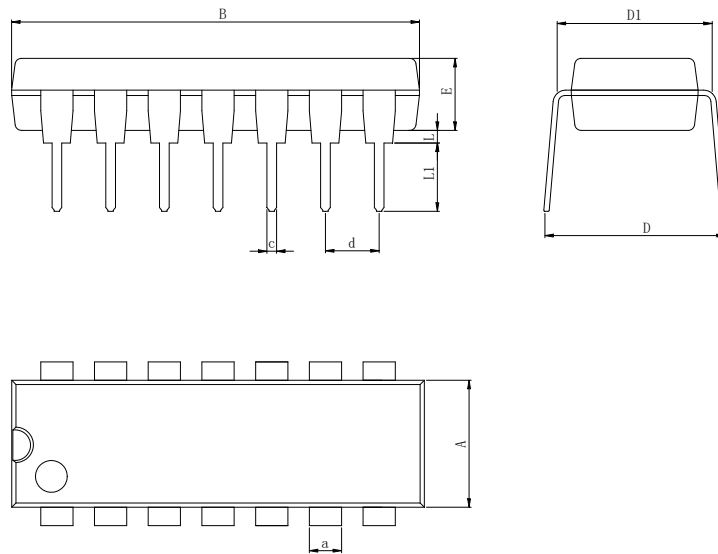
TSSOP-14



Dimensions In Millimeters(TSSOP-14)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	

PHYSICAL DIMENSIONS

DIP-14



Dimensions In Millimeters(DIP-14)

Symbol:	A	B	D	D1	E	L	L1	a	c	d
Min:	6.10	18.94	8.10	7.42	3.10	0.50	3.00	1.50	0.40	2.54 BSC
Max:	6.68	19.56	10.9	7.82	3.55	0.70	3.60	1.55	0.50	

REVISION HISTORY

DATE	REVISION	PAGE
2020-3-1	New	1-10
2023-7-21	Update encapsulation type	1
2024-11-1	Update Lead Temperature	3

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